

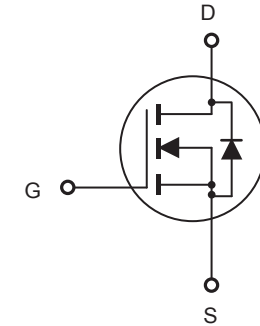


CEP14G04/CEB14G04

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 40V, 140A, $R_{DS(ON)} = 3.6m\Omega$ @ $V_{GS} = 10V$.
 $R_{DS(ON)} = 6.5m\Omega$ @ $V_{GS} = 4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous @ $T_C = 25^\circ C$ @ $T_C = 100^\circ C$	I_D	140	A
		97	A
Drain Current-Pulsed ^a	I_{DM}	560	A
Maximum Power Dissipation @ $T_C = 25^\circ C$ - Derate above $25^\circ C$	P_D	100	W
		0.8	W/ $^\circ C$
Single Pulsed Avalanche Energy ^e	E_{AS}	320	mJ
Single Pulsed Avalanche Current ^e	I_{AS}	80	A
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.5	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ C/W$



CEP14G04/CEB14G04

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
On Characteristics ^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$		3	3.6	$m\Omega$
		$V_{GS} = 4.5V, I_D = 40A$		5	6.5	$m\Omega$
Dynamic Characteristics ^d						
Input Capacitance	C_{iss}	$V_{DS} = 20V, V_{GS} = 0V, f = 1.0\text{ MHz}$		3730		pF
Output Capacitance	C_{oss}			570		pF
Reverse Transfer Capacitance	C_{rss}			360		pF
Switching Characteristics ^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20V, I_D = 20A, V_{GS} = 10V, R_{GEN} = 1.6\Omega$		21	42	ns
Turn-On Rise Time	t_r			12	24	ns
Turn-Off Delay Time	$t_{d(off)}$			83	166	ns
Turn-Off Fall Time	t_f			19	38	ns
Total Gate Charge	Q_g	$V_{DS} = 20V, I_D = 20A, V_{GS} = 10V$		50	65	nC
Gate-Source Charge	Q_{gs}			10		nC
Gate-Drain Charge	Q_{gd}			24		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				70	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 70A$			1.3	V
Notes : □ a.Repetitive Rating : Pulse width limited by maximum junction temperature.□ b.Surface Mounted on FR4 Board, $t \leq 10\text{ sec.}$ □ c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.□ d.Guaranteed by design, not subject to production testing.□ e.L = 0.1mH, $I_{AS} = 80A, V_{DD} = 24V, R_G = 25\Omega$, Starting $T_J = 25\text{ C}$ □						



CEP14G04/CEB14G04

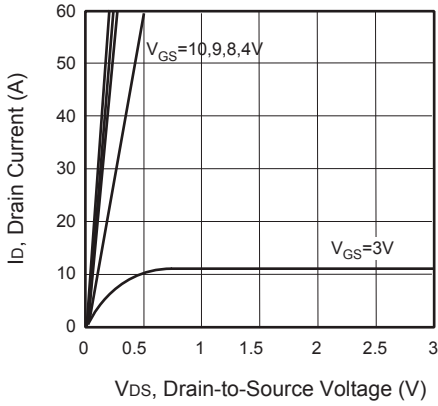


Figure 1. Output Characteristics

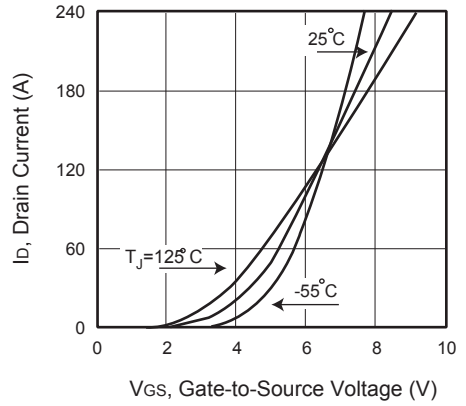


Figure 2. Transfer Characteristics

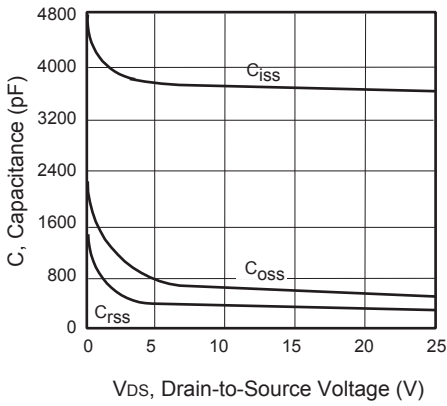


Figure 3. Capacitance

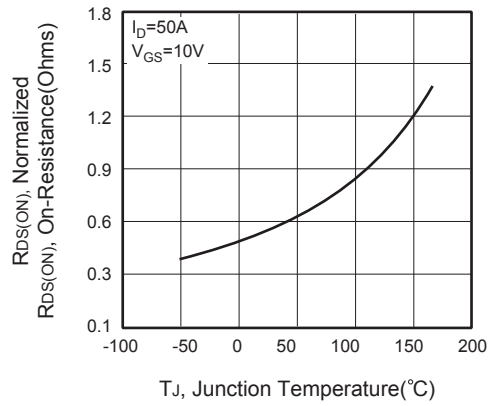


Figure 4. On-Resistance Variation with Temperature

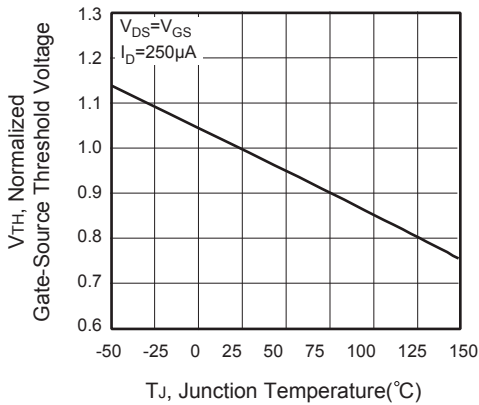


Figure 5. Gate Threshold Variation with Temperature

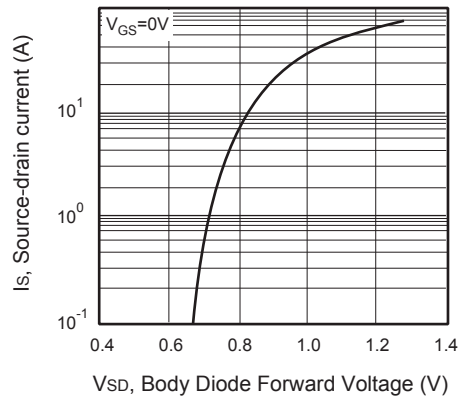


Figure 6. Body Diode Forward Voltage Variation with Source Current



CEP14G04/CEB14G04

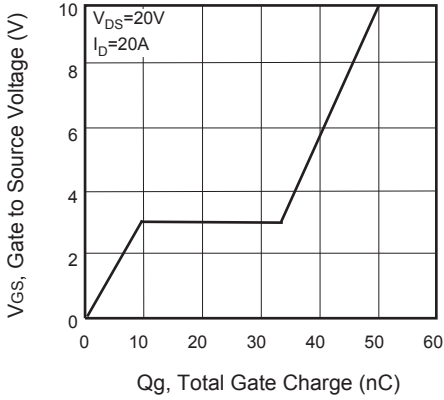


Figure 7. Gate Charge

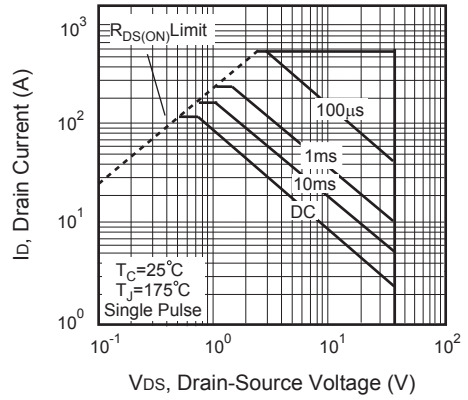


Figure 8. Maximum Safe Operating Area

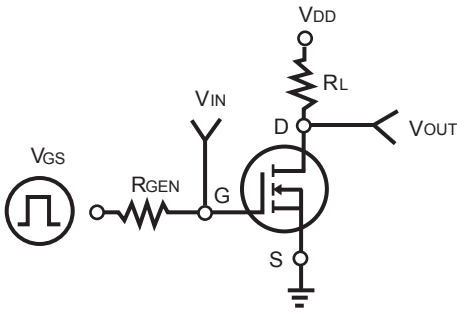


Figure 9. Switching Test Circuit

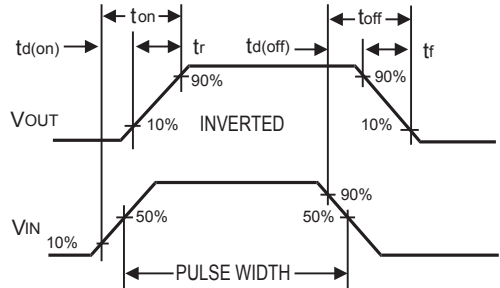


Figure 10. Switching Waveforms

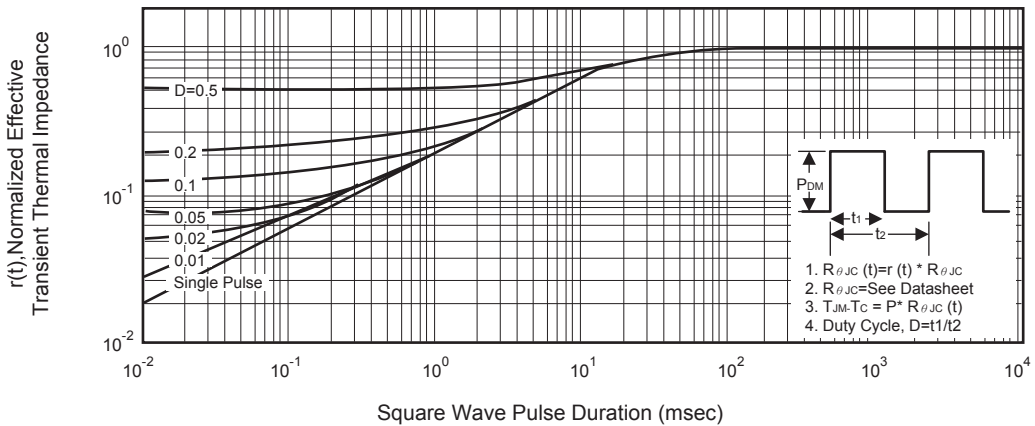


Figure 11. Normalized Thermal Transient Impedance Curve